This Sheet Has Been Replaced

METHOD FOR FORMING A TAPERED OPENING IN SILICON

Abstract of the Disclosure

A method for forming a tapered opening in a silicon substrate uses NF_3 and HBr. The NF_3/HBr plasma etch allows both a good taper profile, 85° to 60°, as well as a good etch rate, approximately 2500 to 3000 Å/minute. Although not limited to a particular trench size, the present method is well suited for forming openings smaller than 0.45 μm.